FDMS001N025DSD

PowerTrench® Power Clip

25 V Asymmetric Dual N−Channel MOSFET

General Description

This device includes two specialized N−Channel MOSFETs in a dual package. The switch node has been internally connected to enable easy placement and routing of synchronous buck converters. The control MOSFET (Q1) and synchronous SyncFET (Q2) have been designed to provide optimal power efficiency.

Features

Q1: N−Channel

- Max $r_{DS(on)}$ = 3.25 mΩ at V_{GS} = 10 V, I_D = 19 A
- Max $r_{DS(on)}$ = 4 mΩ at V_{GS} = 4.5 V, I_D = 17 A

Q2: N−Channel

- Max $r_{DS(on)}$ = 0.92 mΩ at V_{GS} = 10 V, I_D = 38 A
- Max $r_{DS(on)}$ = 1.20 mΩ at V_{GS} = 4.5 V, I_D = 34 A
- Low Inductance Packaging Shortens Rise/Fall Times, Resulting in Lower Switching Losses
- MOSFET Integration Enables Optimum Layout for Lower Circuit Inductance and Reduced Switch Node Ringing
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Computing
- Communications
- General Purpose Point of Load

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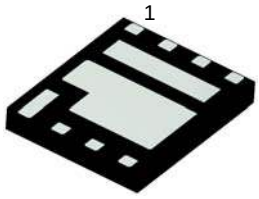

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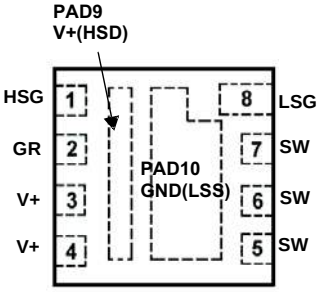
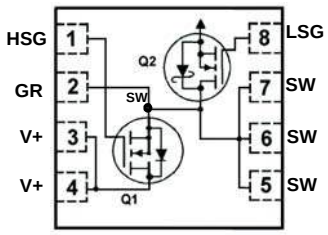
CASE 483AR





PIN ASSIGNMENT

Pin	Name	Description
1	HSG	High Side Gate
2	GR	Gate Return
3,4,9	V+(HSD)	High Side Drain
5,6,7	SW	Switching Node, Low Side Drain
8	LSG	Low Side Gate
10	GND(LSS)	Low Side Source

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

Table 1. MAXIMUM RATINGS T_A = 25°C unless otherwise noted

Symbol	Parameter		Q1	Q2	Units
V_{DS}	Drain to Source Voltage		25 (Note 1)	25	V
V_{GS}	Gate to Source Voltage		+16/−12V	+16/−12V	V
I_D	Drain Current −Continuous	T_C = 25°C (Note 2)	69	165	A
	−Continuous	T_C = 100°C (Note 2)	43	104	
	−Continuous	T_A = 25°C	19 (Note 7a)	38 (Note 7b)	
	−Pulsed	T_A = 25°C (Note 3)	381	1240	
E_{AS}	Single Pulse Avalanche Energy	(Note 4)	121	337	mJ
P_D	Power Dissipation for Single Operation	T_C = 25°C	26	42	W
	Power Dissipation for Single Operation	T_A = 25°C	2.1 (Note 7a)	2.3 (Note 7b)	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		−55 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The continuous V_{DS} rating is 25 V; However, a pulse of 30 V peak voltage for no longer than 100 ns duration at 600 KHz frequency can be applied.
2. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro−mechanical application board design.
3. Pulsed Id please refer to Figure 11 and Figure 24 SOA graphs for more details.
4. Q1: E_{AS} of 121 mJ is based on starting T_J = 25°C; N−ch: L = 3 mH, I_{AS} = 9 A, V_{DD} = 25 V. 100% tested at L = 0.1 mH, I_{AS} = 29 A.
   Q2: E_{AS} of 337 mJ is based on starting T_J = 25°C; N−ch: L = 3 mH, I_{AS} = 15 A, V_{DD} = 25 V. 100% tested at L = 0.1 mH, I_{AS} = 48 A.

Table 2. THERMAL CHARACTERISTICS

Symbol	Parameter	Q1	Q2	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.9	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	60 (Note 7a)	55 (Note 7b)	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	130 (Note 7c)	120 (Note 7d)	

Table 3. ELECTRICAL CHARACTERISTICS T_J = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Type	Min	Typ	Max	Units
OFF CHARACTERISTICS							
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 1 mA, V_{GS} = 0 V I_D = 1 mA, V_{GS} = 0 V	Q1 Q2	25 25			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 10 mA, referenced to 25°C I_D = 10 mA, referenced to 25°C	Q1 Q2		15 28		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 20 V, V_{GS} = 0 V V_{DS} = 20 V, V_{GS} = 0 V	Q1 Q2			1 500	μA μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = +16 V/−12 V, V_{DS} = 0 V V_{GS} = +16 V/−12 V, V_{DS} = 0 V	Q1 Q2			±100 ±100	nA nA
ON CHARACTERISTICS							
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 320 μA V_{GS} = V_{DS}, I_D = 1 mA	Q1 Q2	0.8 1.0	1.3 1.5	2.5 3.0	V
$\Delta V_{GS(th)}/\Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 1 mA, referenced to 25°C I_D = 10 mA, referenced to 25°C	Q1 Q2		−4 −3		mV/°C
$r_{DS(on)}$	Drain to Source On Resistance	V_{GS} = 10 V, I_D = 19 A V_{GS} = 4.5 V, I_D = 17 A V_{GS} = 10 V, I_D = 19 A,T_J =125°C	Q1		2.5 3.0 3.5	3.25 4.0 5.0	mΩ
		V_{GS} = 10 V, I_D = 38 A V_{GS} = 4.5 V, I_D = 34 A V_{GS} = 10 V, I_D = 38 A,T_J = 125°C	Q2		0.70 0.92 0.96	0.92 1.20 1.38	

Table 3. ELECTRICAL CHARACTERISTICS T_J = 25°C unless otherwise noted

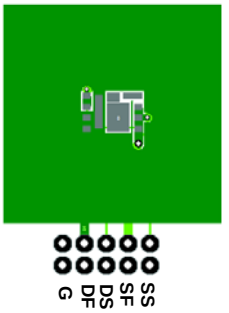
Symbol	Parameter	Test Conditions		Type	Min	Typ	Max	Units
ON CHARACTERISTICS								
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 19 A V_{DS} = 5 V, I_D = 38 A		Q1 Q2		98 262		S
DYNAMIC CHARACTERISTICS								
C_{iss}	Input Capacitance	Q1: V_{DS} = 13 V, V_{GS} = 0 V, f = 1 MHZ Q2: V_{DS} = 13 V, V_{GS} = 0 V, f = 1 MHZ		Q1 Q2		1370 5105		pF
C_{oss}	Output Capacitance			Q1 Q2		625 1810		pF
C_{rss}	Reverse Transfer Capacitance			Q1 Q2		44 173		pF
R_g	Gate Resistance			Q1 Q2	0.1 0.1	0.4 0.3	1.2 1.0	Ω
SWITCHING CHARACTERISTICS								
$t_{d(on)}$	Turn−On Delay Time	Q1: V_{DD} = 13 V, I_D = 19 A, R_{GEN} = 6 Ω Q2: V_{DD} = 13 V, I_D = 38 A, R_{GEN} = 6 Ω		Q1 Q2		8 15	16 26	ns
t_r	Rise Time			Q1 Q2		2 5	10 10	ns
$t_{d(off)}$	Turn−Off Delay Time			Q1 Q2		22 39	34 62	ns
t_f	Fall Time			Q1 Q2		2 4	10 10	ns
Q_g	Total Gate Charge	V_{GS} = 0 V to 10 V	Q1 V_{DD} = 13 V, I_D = 19 A Q2 V_{DD} = 13 V, I_D = 38 A	Q1 Q2		21 75	30 104	nC
Q_g	Total Gate Charge	V_{GS} = 0 V to 4.5 V		Q1 Q2		9.7 35	14 49	nC
Q_{gs}	Gate to Source Gate Charge			Q1 Q2		2.9 12		nC
Q_{gd}	Gate to Drain “Miller” Charge			Q1 Q2		2.0 7.9		nC
DRAIN−SOURCE DIODE CHARACTERISTICS								
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 19 A (Note 6) V_{GS} = 0 V, I_S = 38 A (Note 6)		Q1 Q2		0.8 0.8	1.2 1.2	V
I_S	Diode continuous forward current	T_C = 25°C (Note 2)		Q1 Q2			69 125	A
$I_{S,Pulse}$	Diode pulse current	T_C = 25°C (Note 3)		Q1 Q2			381 1240	A
t_{rr}	Reverse Recovery Time	Q1 I_F = 19 A, di/dt = 100 A/μs Q2 I_F = 38 A, di/dt = 300 A/μs		Q1 Q2		27 39	44 62	ns
Q_{rr}	Reverse Recovery Charge			Q1 Q2		12 55	21 87	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

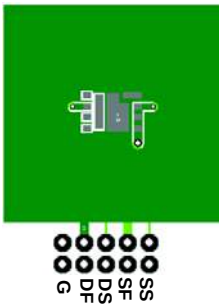
5. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR−4 material. $R_{\theta CA}$ is determined by the user’s board design.
6. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.

PACKAGE MARKING AND ORDERING INFORMATION

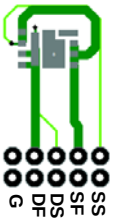
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS001N025DSD	FDMS001N025DSD	Power Clip 56	13”	12 mm	3000 units



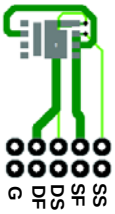
(Note 7a)



(Note 7b)



(Note 7c)



(Note 7d)

7. a) 60°C/W when mounted on a 1 in^2 pad of 2 oz copper
   b) 55°C/W when mounted on a 1 in^2 pad of 2 oz copper
   c) 130°C/W when mounted on a minimum pad of 2 oz copper
   d) 120°C/W when mounted on a minimum pad of 2 oz copper

TYPICAL CHARACTERISTICS (Q1 N−Channel) T_J = 25°C unless otherwise noted

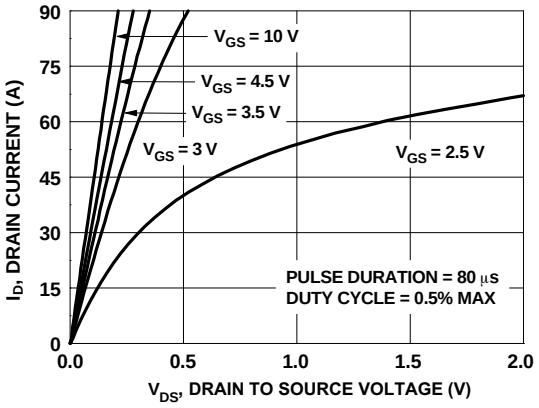


Figure 1. On Region Characteristics

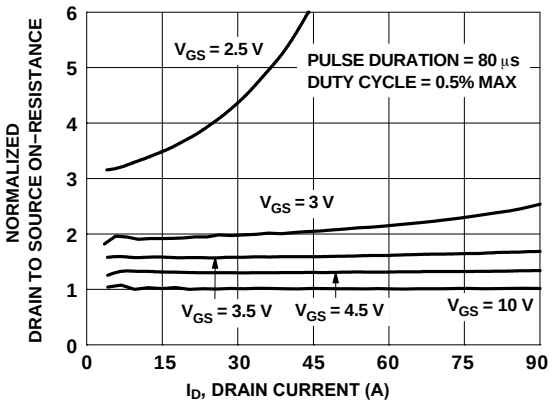


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

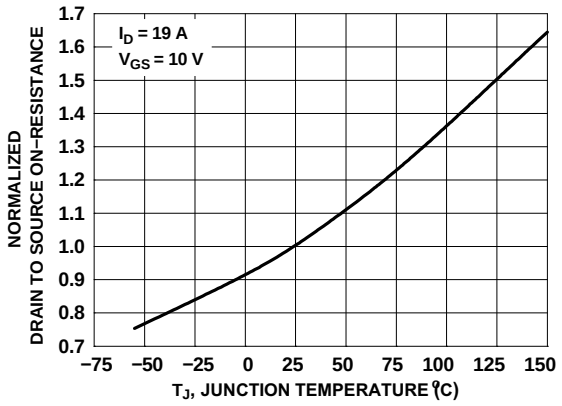


Figure 3. Normalized On Resistance vs. Junction Temperature

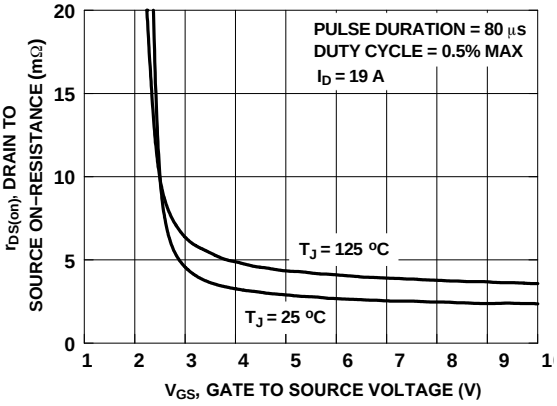


Figure 4. On−Resistance vs. Gate to Source Voltage

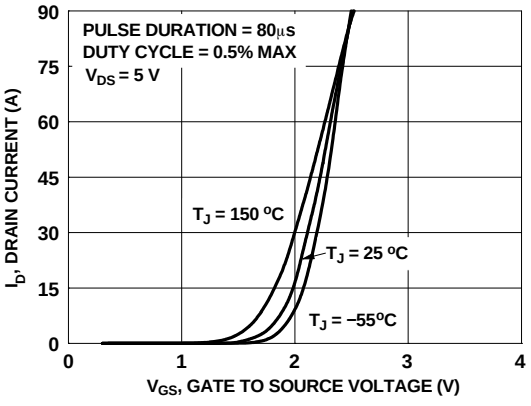


Figure 5. Transfer Characteristics

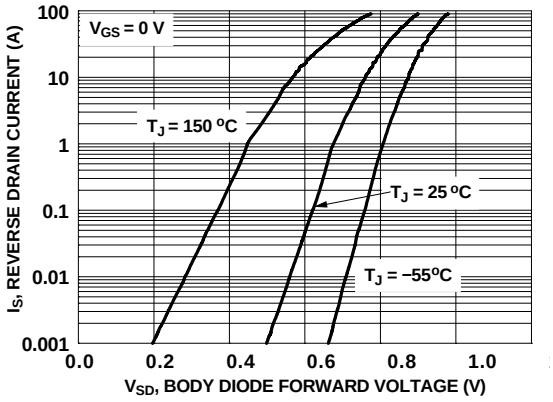


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q1 N−Channel) T_J = 25°C unless otherwise noted

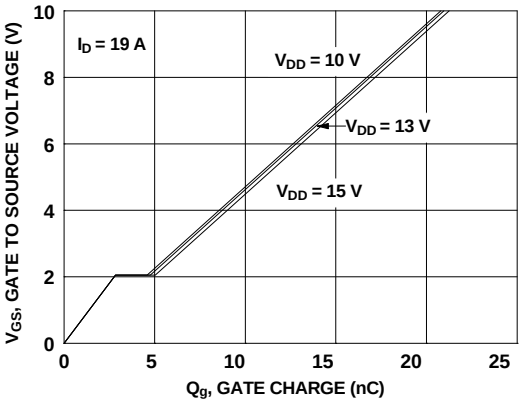


Figure 7. Gate Charge Characteristics

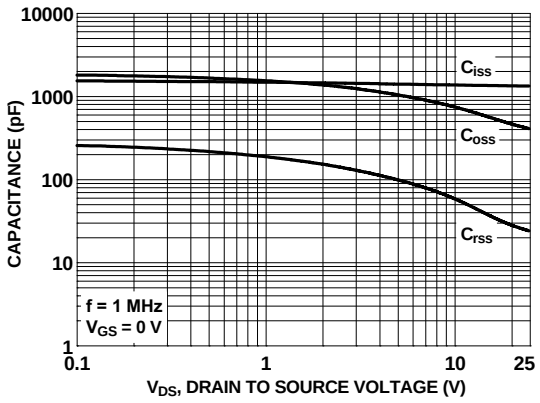


Figure 8. Capacitance vs. Drain to Source Voltage

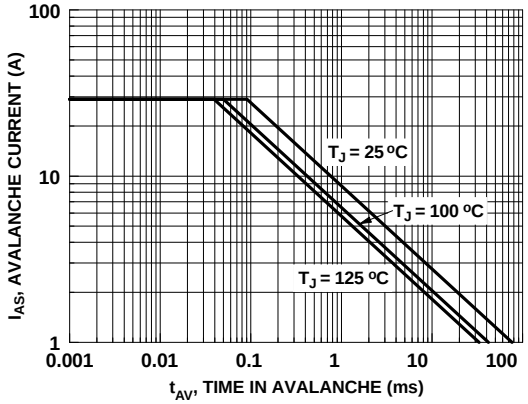


Figure 9. Unclamped Inductive Switching Capability

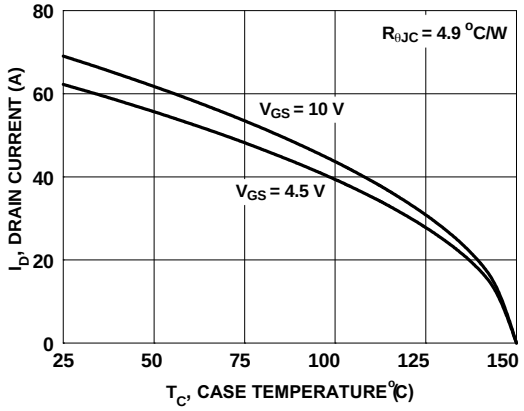


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

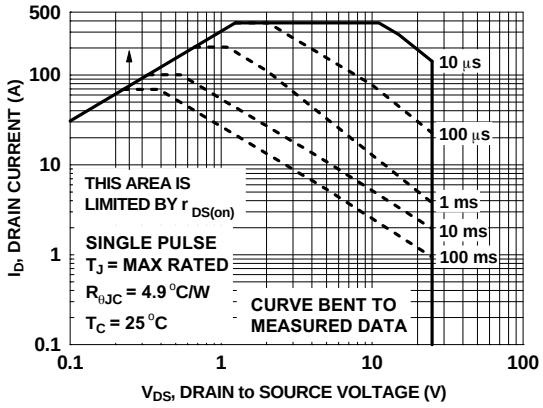


Figure 11. Forward Bias Safe Operating Area

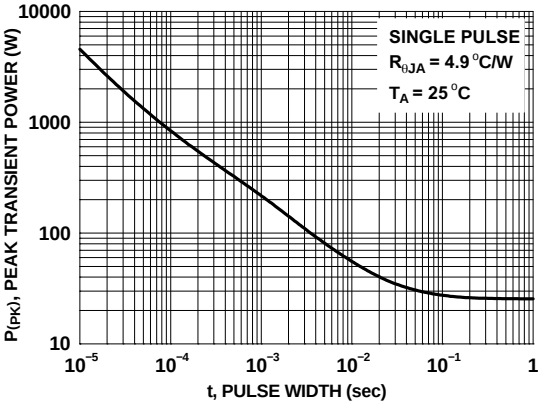


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q1 N−Channel) T_J = 25°C unless otherwise noted

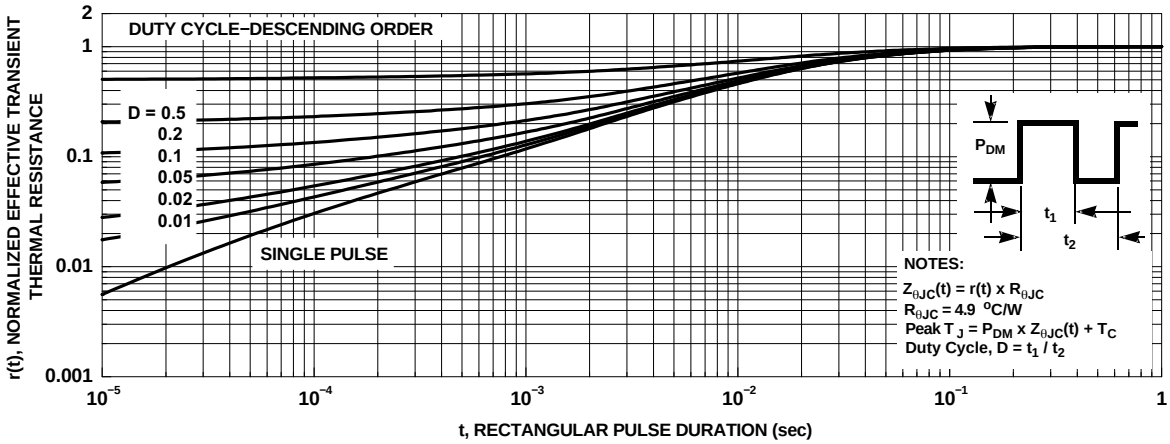


Figure 13. Junction−to−Case Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (Q2 N−Channel) T_J = 25°C unless otherwise noted

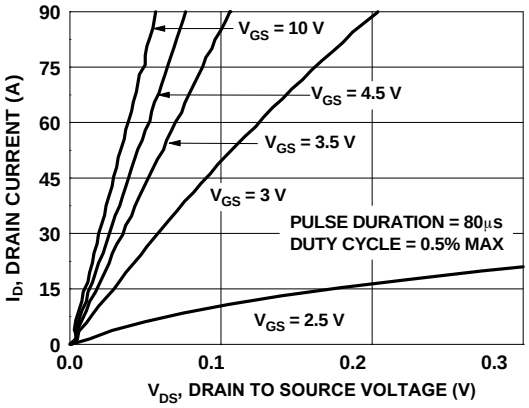


Figure 14. On Region Characteristics

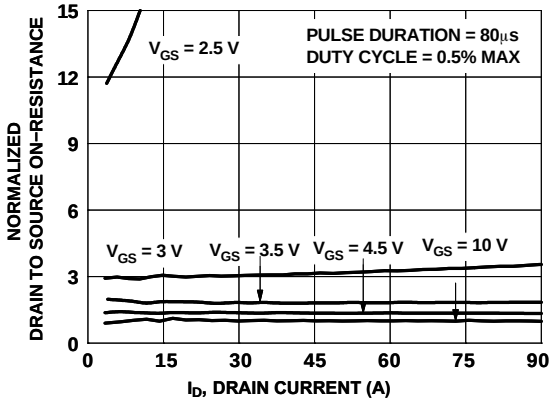


Figure 15. Normalized On−Resistance vs. Drain Current and Gate Voltage

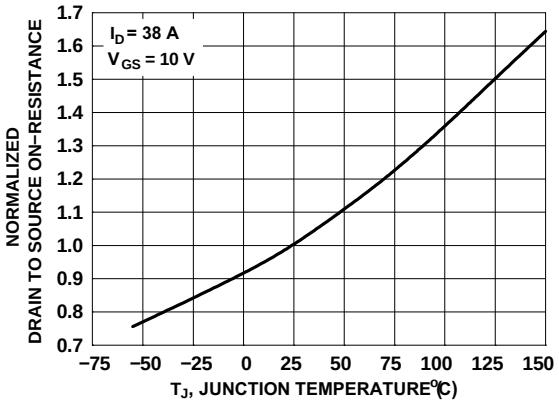


Figure 16. Normalized On Resistance vs. Junction Temperature

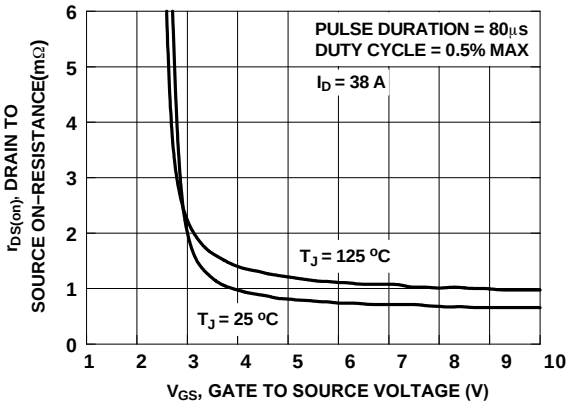


Figure 17. On−Resistance vs. Gate to Source Voltage

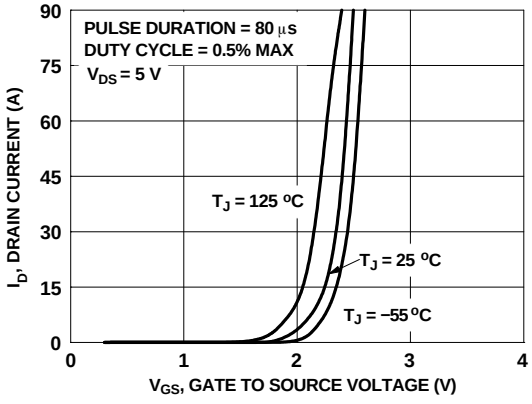


Figure 18. Transfer Characteristics

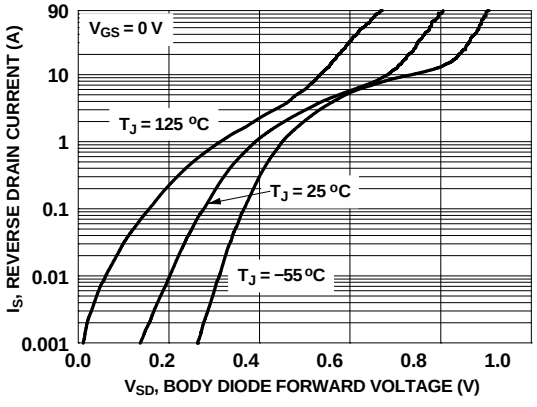


Figure 19. Source to Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS (Q2 N−Channel) T_J = 25°C unless otherwise noted

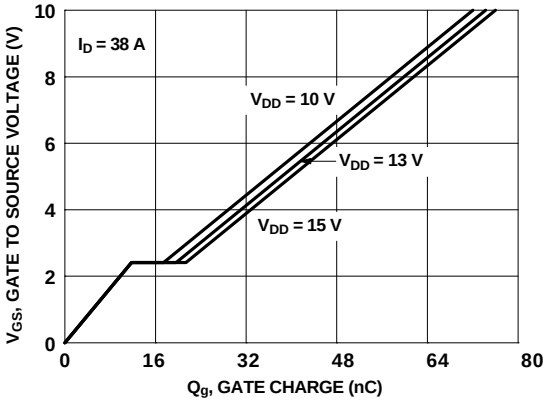


Figure 20. Gate Charge Characteristics

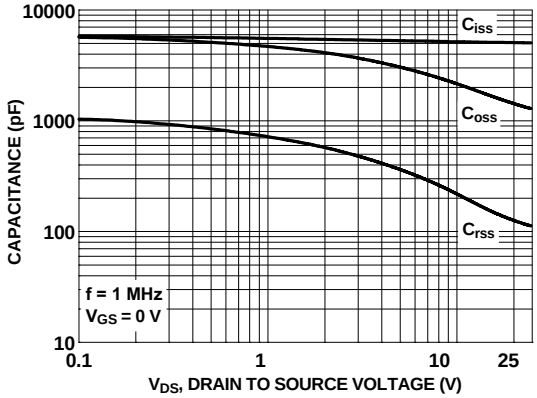


Figure 21. Capacitance vs. Drain to Source Voltage

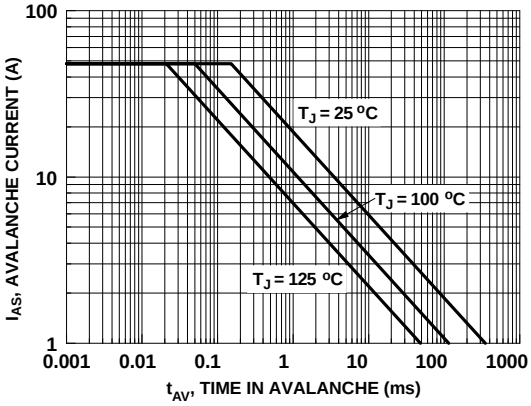


Figure 22. Unclamped Inductive Switching Capability

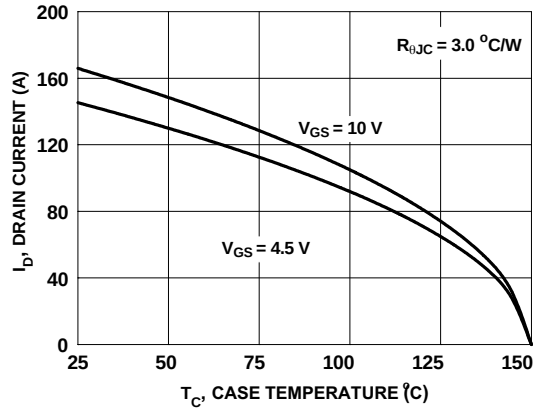


Figure 23. Maximum Continuous Drain Current vs. Case Temperature

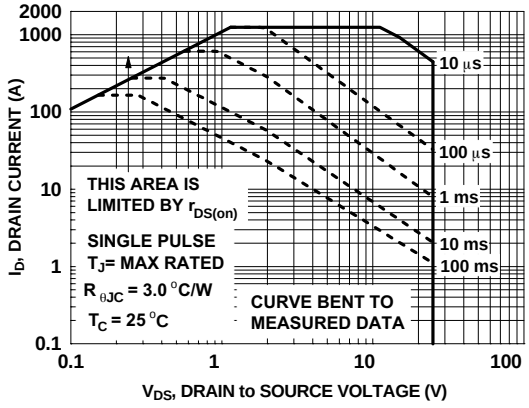


Figure 24. Forward Bias Safe Operating Area

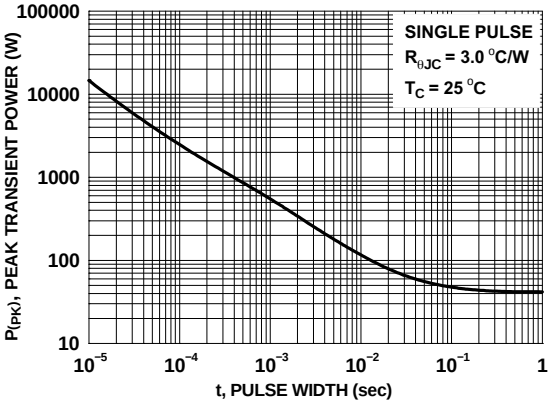


Figure 25. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS (Q2 N−Channel) T_J = 25°C unless otherwise noted

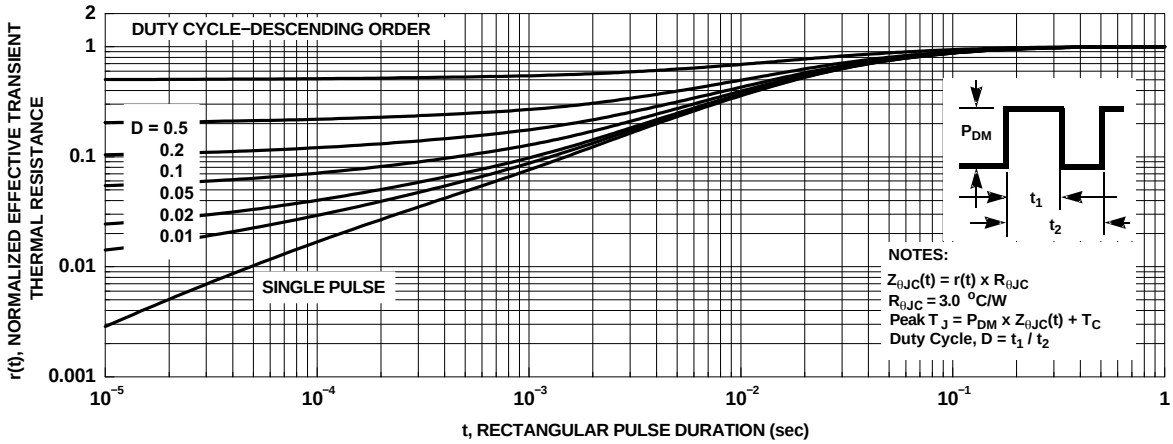


Figure 26. Junction−to−Case Transient Thermal Response Curve

TYPICAL CHARACTERISTICS (continued)

ON Semiconductor's SyncFET process embeds a Schottky diode in parallel with PowerTrench MOSFET. This diode exhibits similar characteristics to a discrete external Schottky diode in parallel with a MOSFET. Figure 27 shows the reverses recovery characteristic of the FDMS001N025DSD.

Schottky barrier diodes exhibit significant leakage at high temperature and high reverse voltage. This will increase the power in the device.

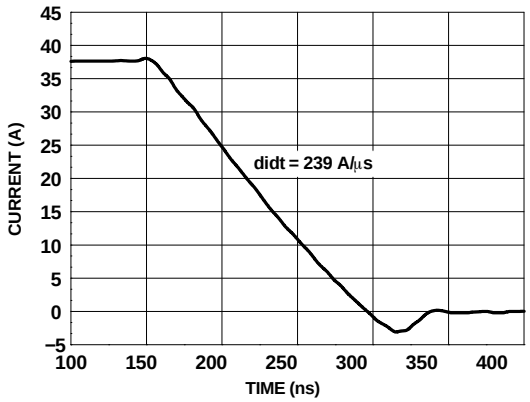


Figure 27. FDMS001N025DSD SyncFET Body Diode Reverse Recovery Characteristic

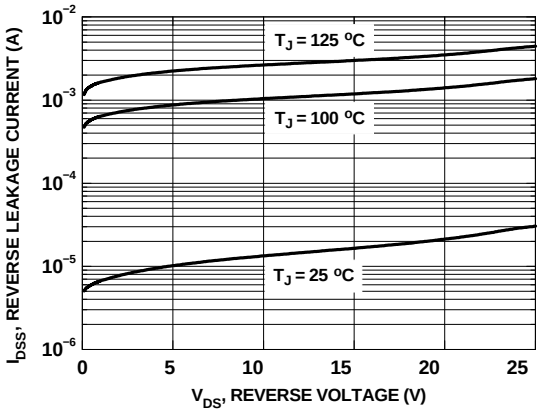
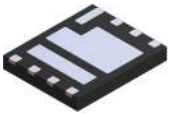


Figure 28. SyncFET Body Diode Reverse Leakage vs. Drain−Source Voltage

MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS

ON Semiconductor®



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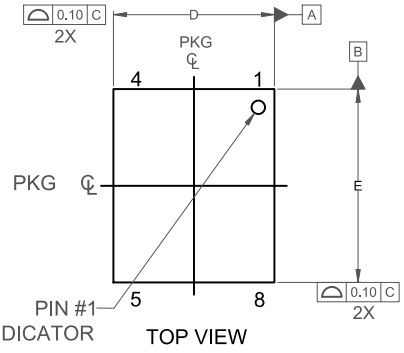

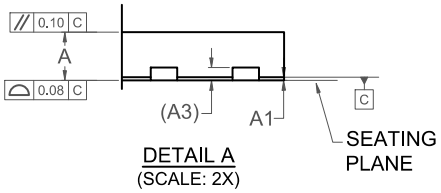

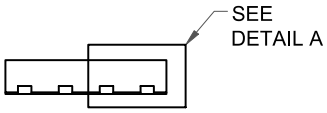

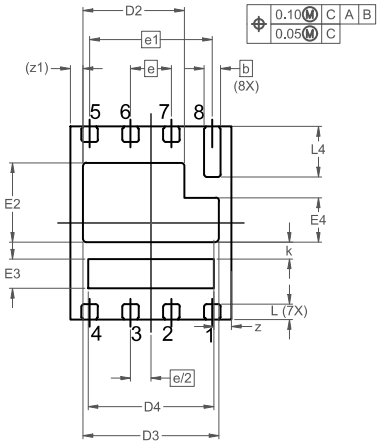

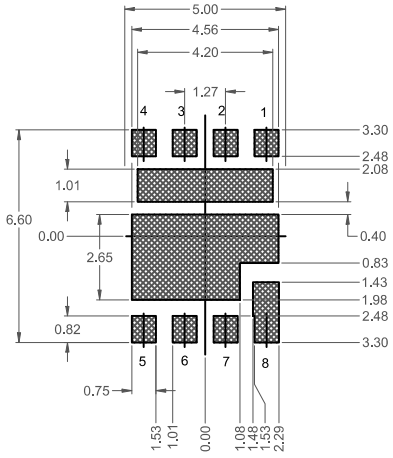

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTES: UNLESS OTHERWISE SPECIFIED

A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229, DATED 11/2001.
B) ALL DIMENSIONS ARE IN MILLIMETERS.
C) DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.00	-	0.05
A3	0.20 REF		
b	0.51 BSC		
D	4.90	5.00	5.10
D2	3.05	3.15	3.25
D3	4.12	4.22	4.32
D4	3.80	3.90	4.00
E	5.90	6.00	6.10
E2	2.36	2.46	2.56
E3	0.81	0.91	1.01
E4	1.27	1.37	1.47
e	1.27 BSC		
e/2	0.635 BSC		
e1	3.81 BSC		
k	0.42	0.52	0.62
L	0.38	0.48	0.58
L4	1.47	1.57	1.67
z	0.55 REF		
z1	0.39 REF		

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